



ZXTN07045EFF

45V NPN LOW SATURATION TRANSISTOR

Features

- BV_{CEO} > 45V
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage V_{CE(sat)} < 80mV @ 1A
- R_{CE(sat)} = 50mΩ
- h_{FE} Characterised up to 4A
- High h_{FE} Min 400 @ 1A
- 1.5W Power Dissipation
- Complementary PNP Type: ZXTP07040DFF
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 and 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

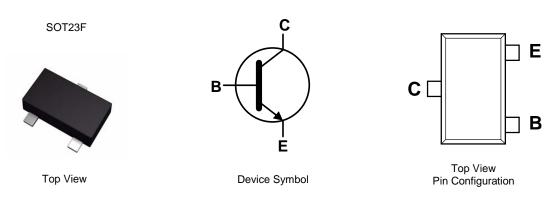
This low voltage NPN transistor has been designed for applications requiring high gain and very low saturation voltage. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

Mechanical Data

- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.012 grams (Approximate)

Applications

- Boost Converters
- MOSFET and IGBT Gate Drivers
- Lamp and Relay Driver
- Motor Drive
- Siren Driver



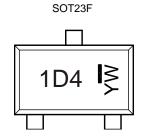
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN07045EFFTA	AEC-Q101	1D4	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1D4 = Product Type Marking Code YW = Date Code Marking Y = Year : 0~9

 \overline{W} = Week : A~Z : 1~26 a~z : 27~52

z represents 52 & 53 week



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	45	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	4	А
Peak Pulse Current	I _{CM}	6	Α
Base Current	I _B	1	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.84 6.72		
Power Dissipation	(Note 6)		1.34 10.72	W mW/°C	
Linear Derating Factor	(Note 7)	- P _D	1.50 12.0		
	(Note 8)]	2.0 16.0		
	(Note 5)		149		
Thermal Desigtance, Junction to Ambient	(Note 6)		93		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	83	°C/W	
	(Note 8)		60		
Thermal Resistance, Junction to Lead	(Note 9)	R _{0JL}	43.77	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

Notes:

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured

under still air conditions whilst operating in a steady-state.

^{6.} Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper. 7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.

Same as Note 5, except the device is mounted on 50
 Same as Note 7, whilst measured at t < 5 seconds.

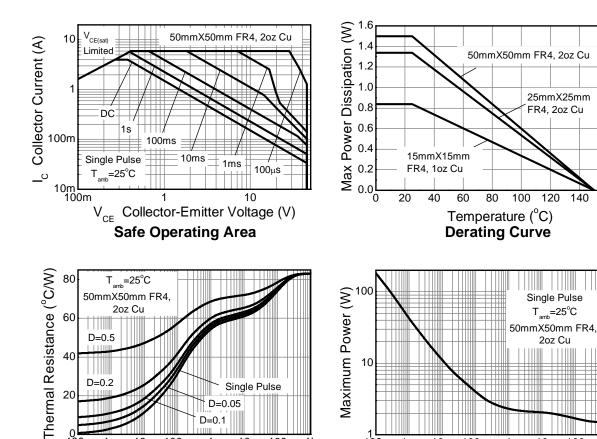
^{9.} Thermal resistance from junction to solder-point (at the end of the collector lead).

^{10.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.

140 160



Thermal Characteristics and Derating Information



Transient Thermal Impedance

Pulse Width (s)

10m 100m

10

100

Pulse Width (s) **Pulse Power Dissipation**

10

100

100m

100μ



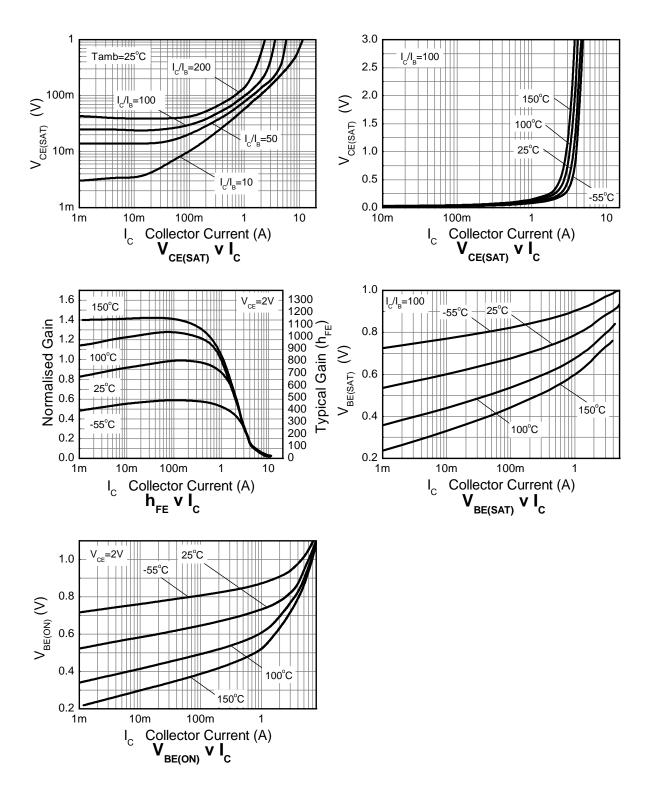
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	45	160	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	45	60	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	_	V	$I_E = 100\mu A$
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	8.2	_	V	$I_E = 100\mu A$; $R_{BC} < 1k\Omega$ or $-0.25V < V_{BC} < 0.25V$
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	6	7.2	_	V	I _E = 100μA
Collector-Base Cut-Off Current	Ісво	_	<1 —	50 20	nΑ μΑ	V _{CB} = 35V V _{CB} = 35V, T _A = +100°C
Emitter-Base Cut-Off Current	I _{EBO}	_	<1	50	nA	V _{EB} = 5.6V
ON CHARACTERISTICS (Note 11)						•
Static Forward Current Transfer Ratio	h _{FE}	500 400 250 70	800 710 530 125	1500 — — —	_	$\begin{split} I_{C} &= 100 \text{mA}, \ V_{CE} = 2 V \\ I_{C} &= 1 \text{A}, \ V_{CE} = 2 V \\ I_{C} &= 2 \text{A}, \ V_{CE} = 2 V \\ I_{C} &= 4 \text{A}, \ V_{CE} = 2 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE} (sat)	_	45 160 60 200 230	70 230 80 270 280	mV	$I_C = 0.1A, I_B = 0.5mA$ $I_C = 1A, I_B = 5mA$ $I_C = 1A, I_B = 100mA$ $I_C = 2A, I_B = 20mA$ $I_C = 4A, I_B = 200mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	1000	1100	mV	I _C = 4A, I _B = 200mA
Base-Emitter On Voltage	V _{BE(on)}	_	875	1000	mV	I _C = 4A, V _{CE} = 2V
SMALL SIGNAL CHARACTERISTICS	1 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \					
Transition Frequency	f⊤	150	190	_	MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, $f = 50$ MHz
Input Capacitance	C _{ibo}	_	225	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	18.4	25	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _d	_	22.3	_	ns	101/
Rise Time	t _r	_	10.6	_	ns	$V_{CC} = 10V$
Storage Time	t _s	_	613	_	ns	$I_{C} = 500 \text{mA},$ $I_{B1} = I_{B2} = 50 \text{mA}$
Fall Time	t _f	_	146	_	ns	TIB1 = IB2 = SUITIA

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

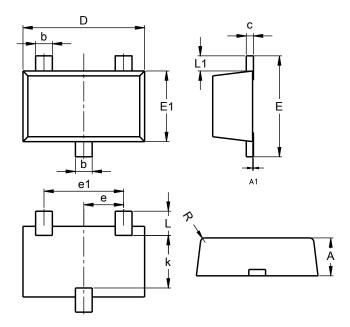




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F

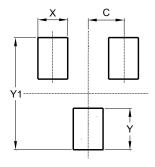


SOT23F					
Dim	Min Max Typ				
Α	0.80	1.00	0.90		
b	0.35	0.50	0.44		
С	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1	0.190 REF				
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20				
L	0.30 0.65 0.50				
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F



Dimensions	(in mm)		
С	0.95		
Х	0.80		
Υ	1.110		
Y1	3.000		



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